

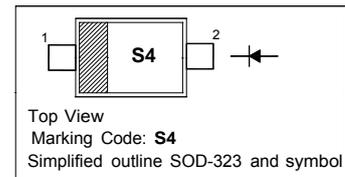
## Surface Mount Schottky Barrier Diodes

### Features

- Low Forward Voltage

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	$V_{RRM}$	SD103AWS SD103BWS SD103CWS	40 30 20	V
Reverse Voltage		SD103AWS SD103BWS SD103CWS	40 30 20	V
Average Forward Rectified Current		$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\text{ s}$	$I_{FSM}$	2	A	
Power Dissipation	$P_{tot}$	200	mW	
Operating and Storage Temperature Range	$T_j, T_{stg}$	- 65 to + 125	$^\circ\text{C}$	

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	SD103AWS SD103BWS SD103CWS	40 30 20	- - -	V	
Reverse Leakage Current at $V_R = 30\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 10\text{ V}$		SD103AWS SD103BWS SD103CWS	- - -	- - -	5 5 5	$\mu\text{A}$
Forward Voltage at $I_F = 20\text{ mA}$ at $I_F = 200\text{ mA}$		$V_F$	- -	- -	0.37 0.6	V
Total Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	-	50	-	pF	
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$ , $t_{rr} = 0.1\text{ }I_R$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	-	10	-	ns	

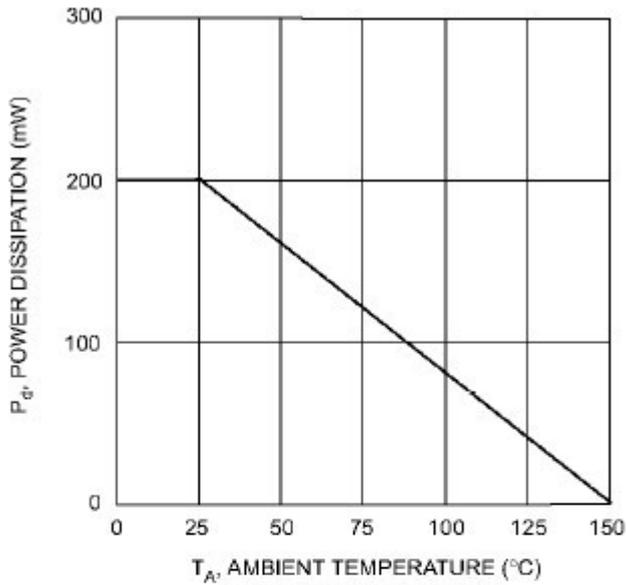


Fig. 1 Power Derating Curve

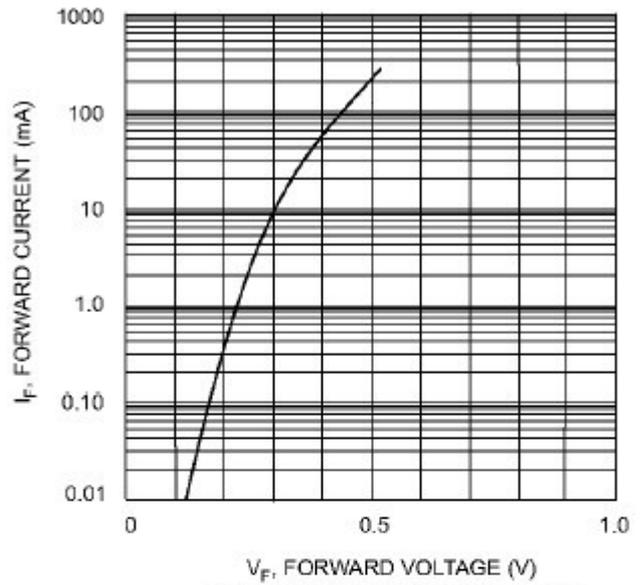


Fig. 2 Typical Forward Characteristics

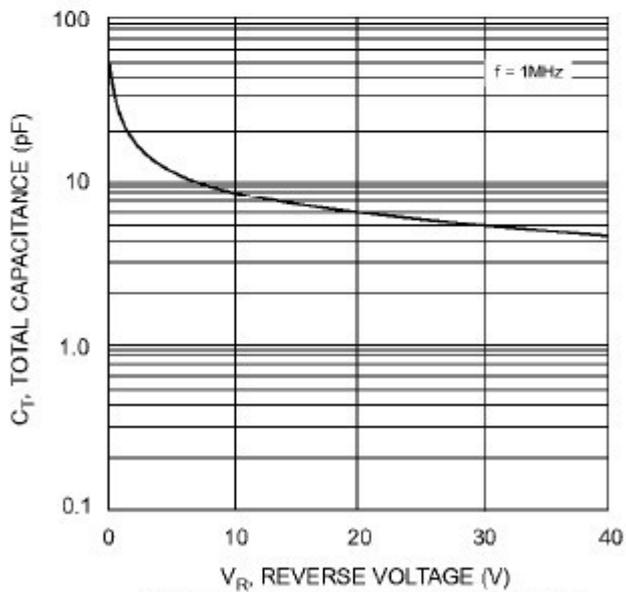


Fig. 3 Total Capacitance vs Reverse Voltage